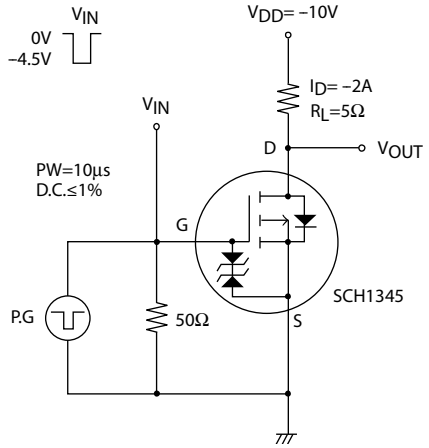
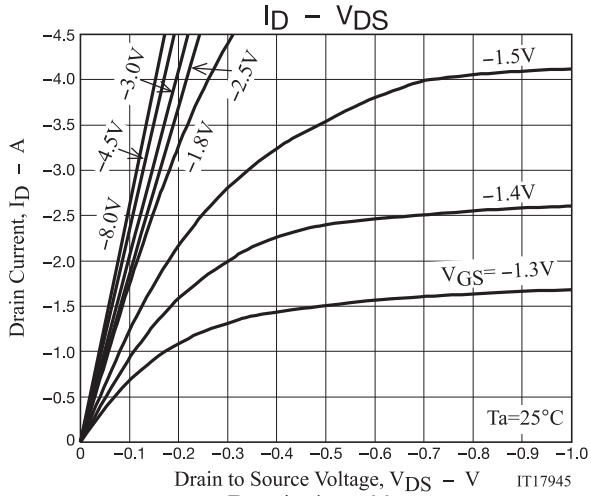
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

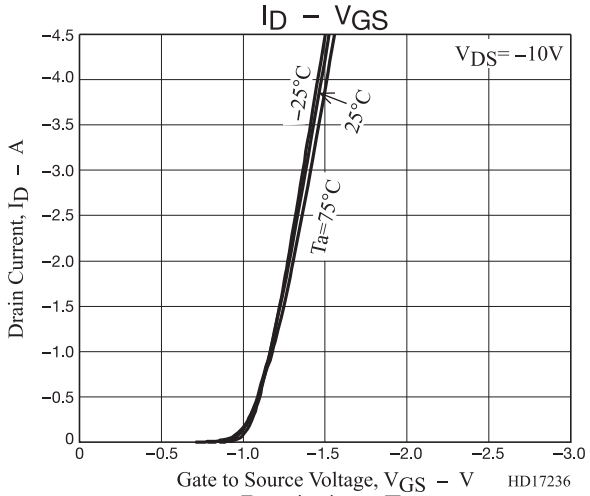
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=–1mA, V_{GS}=0V	–20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=–20V, V_{GS}=0V			–1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	V_{GS}(th)	V_{DS}=–10V, I_D=–1mA	–0.4		–1.3	V
Forward Transconductance	g_{FS}	V_{DS}=–10V, I_D=–2A		6		S
Static Drain to Source On-State Resistance	R_{DS}(on)1	I_D=–2A, V_{GS}=–4.5V		42	49	mΩ
	R_{DS}(on)2	I_D=–1A, V_{GS}=–2.5V		53	64	mΩ
	R_{DS}(on)3	I_D=–0.5A, V_{GS}=–1.8V		65	85	mΩ
	R_{DS}(on)4	I_D=–0.5A, V_{GS}=–1.5V		74	120	mΩ
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		1220		pF
Output Capacitance	Coss			82		pF
Reverse Transfer Capacitance	Crss			72		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit		8.8		ns
Rise Time	t_r			35		ns
Turn-OFF Delay Time	t_{d}(off)			123		ns
Fall Time	t_f			61		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=–4.5V, I_D=–4.5A		11		nC
Gate to Source Charge	Qgs			1.9		nC
Gate to Drain “Miller” Charge	Qgd			1.9		nC
Forward Diode Voltage	V_{SD}	I_S=–4.5A, V_{GS}=0V		–0.82	–1.2	V

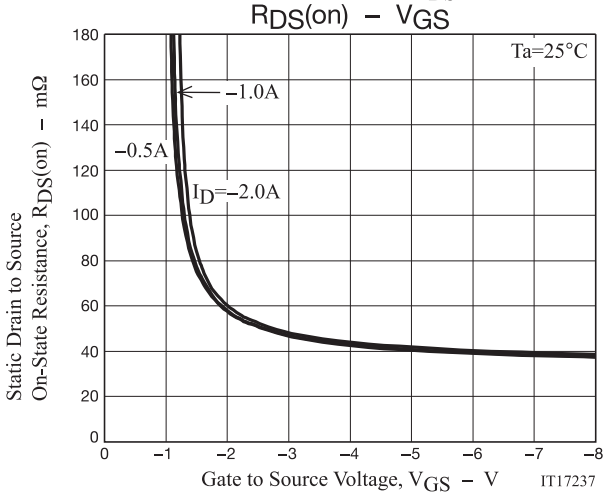
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

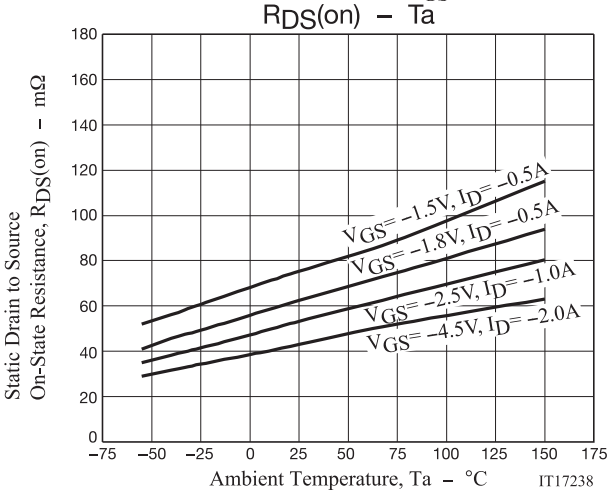
Switching Time Test Circuit

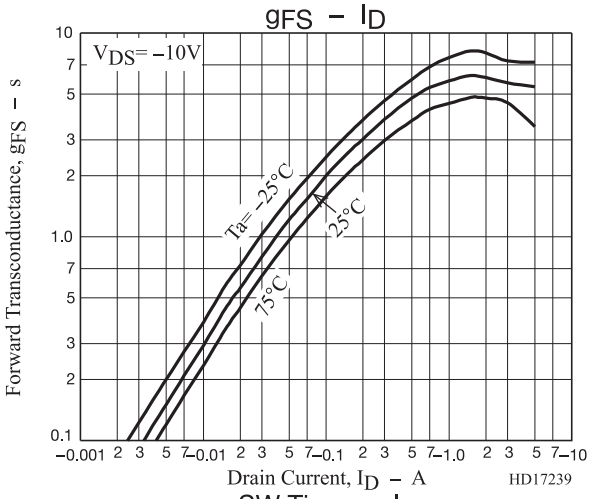


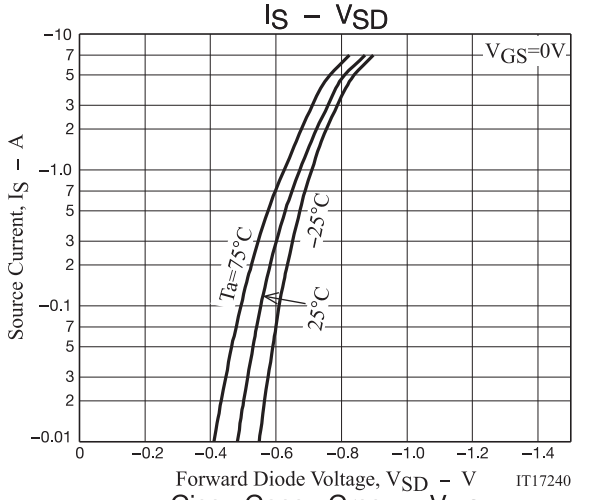


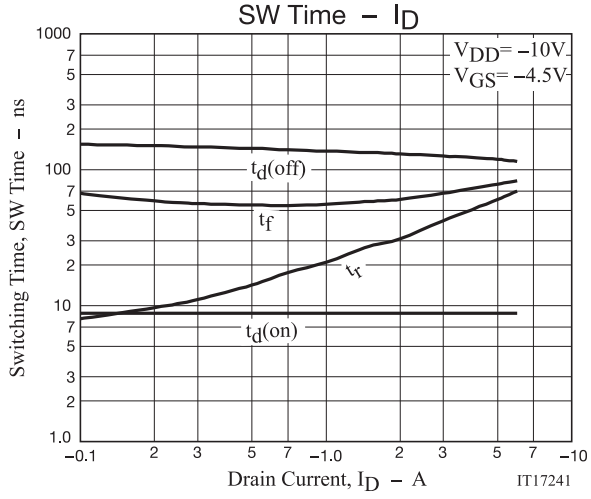


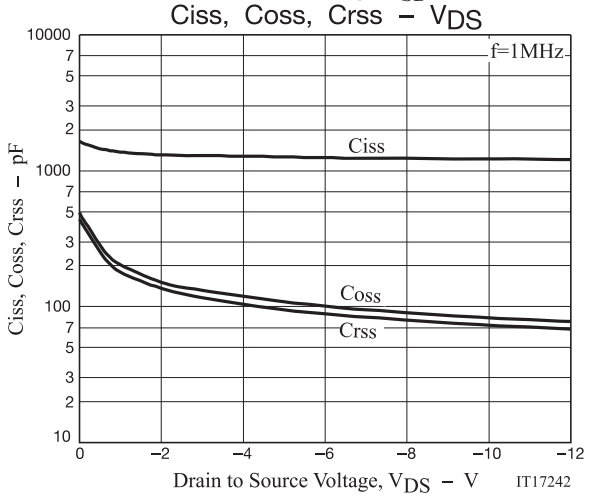


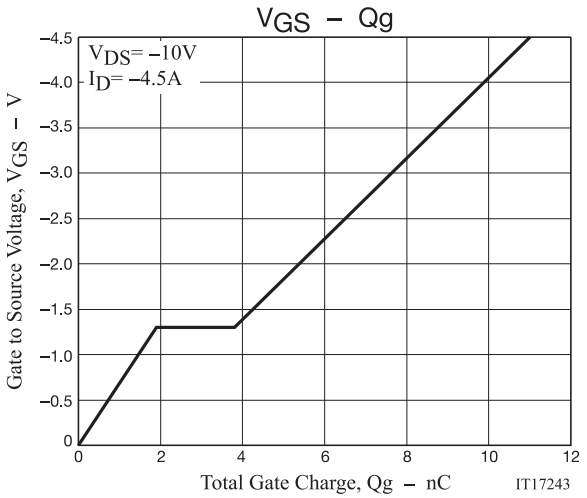


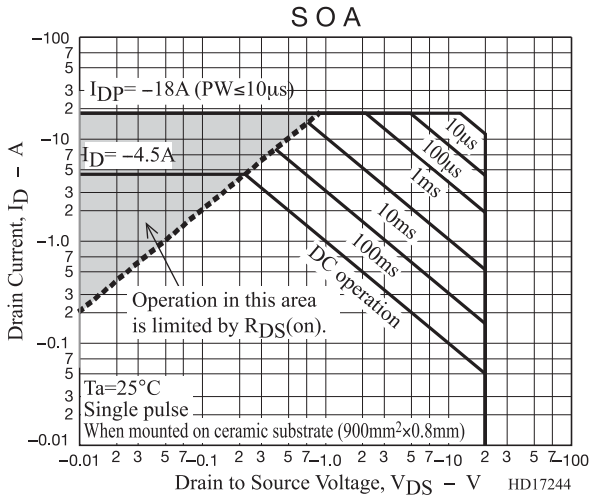


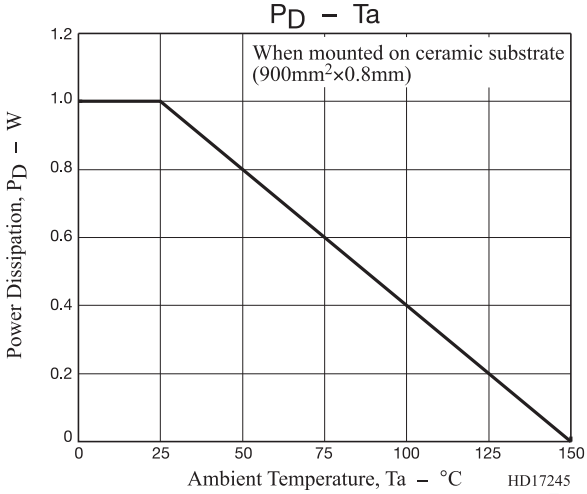


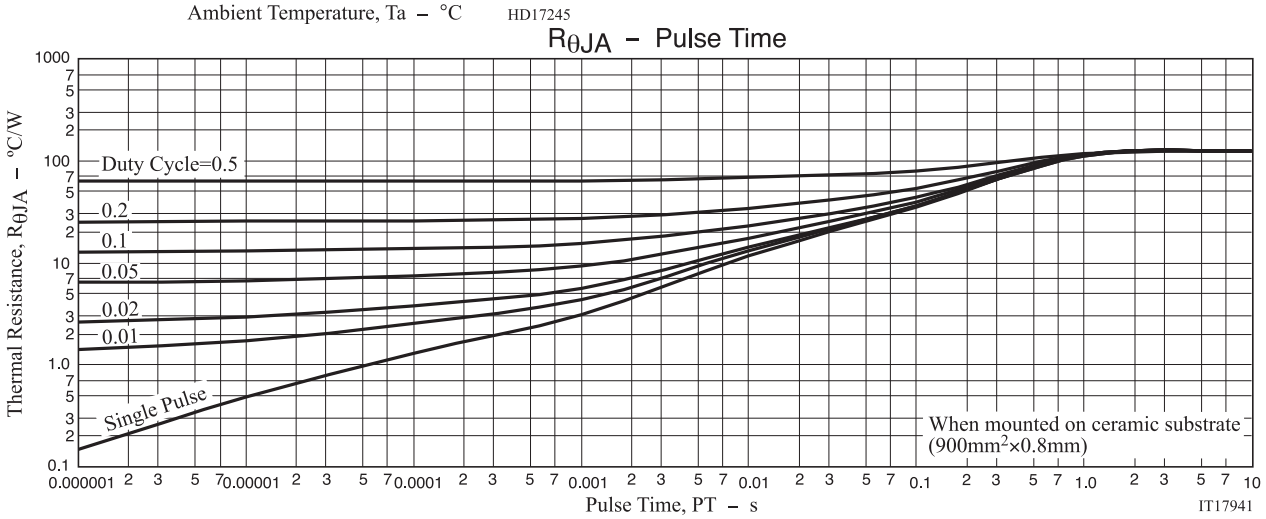








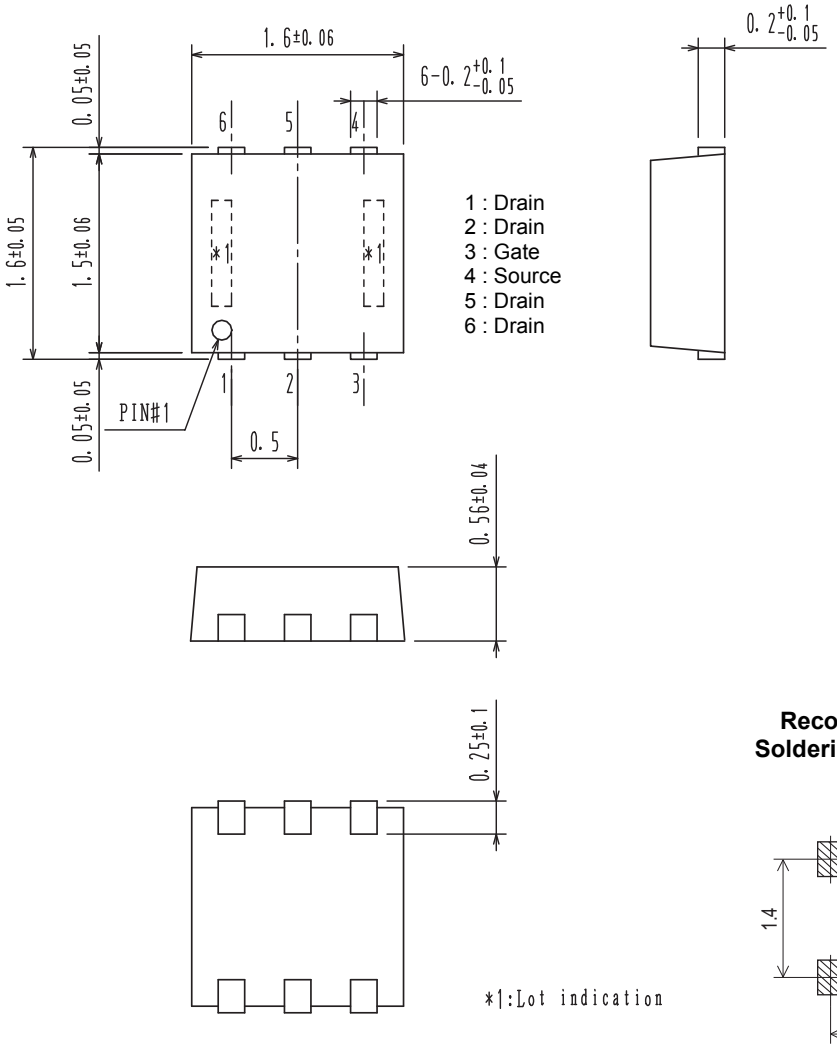




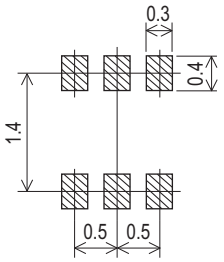
PACKAGE DIMENSIONS

unit : mm

SOT-563 / SCH6
CASE 463AB
ISSUE O



Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
SCH1345-TL-H	YW	SOT-563 / SCH6 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the SCH1345 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.